Cation Exchange Synthesis of CuIn_xGa_{1-x}Se₂ Nanowires and Their

Implementation in Photovoltaic Devices†

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Fig. S1 Bi nanoparticles used for the synthesis of CuInSe₂ nanowires.



Fig. S2 TEM images of (a) $CuIn_{0.98}Ga_{0.02}Se_2$ nanowires and (b) $CuIn_{0.89}Ga_{0.11}Se_2$ nanowires



Fig. S3 TEM images of the product when the $Ga/CuInSe_2$ mole ratio in the reaction mixture is 8:1



Fig. S4 Room temperature absorbance spectra of (a) $CuIn_{0.98}Ga_{0.02}Se_2$ nanowires and (b) $CuIn_{0.89}Ga_{0.11}Se_2$ nanowires dispersed in toluene.